

Substitute form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	To Be Assigned 10/760966
				Filing Date	Concurrently Herewith 1-20-04
				First Named Inventor	Zhibo Zhang
				Group Art Unit	2813
				Examiner Name	HOGANS
Sheet 1	of 2	Attorney Docket Number		5051-563DV	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code (if known)			
Dk	1.	6,359,288	B1	Ying et al.	03-19-2002	
	2.	6,231,744	B1	Ying et al.	05-15-2001	
	3.	6,034,468		Wilshaw	03-07-2000	
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	7.	5,306,661		Tonucci et al.	04-1994	
	8.	6,177,291		Eriguchi et al.	01-2001	

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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Office	Number	Kind Code (if known)				
Dk	9.	EP	0 178 831	B1	Alcan International Limited	08-07-1991		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					T
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			
Dk	10.	Auth, Christopher P., "Scaling Theory for Cylindrical, Fully-Depleted, Surrounding-Gate MOSFET's," IEEE Electron Device Letters, Vol. 18, No. 2, February 1997, pp. 74-76			
Dk	11.	Choi et al., "Ultra-thin Body SOI MOSFET for Deep-sub-tenth Micron Era," Department of Electrical Engineering and Computer Sciences, University of California at Berkeley, No Date, 3 pages			
Dk	12.	Hisamoto et al., "A Folded-channel MOSFET for Deep-sub-tenth Micron Era," Department of Electrical Engineering and Computer Sciences, University of California at Berkeley, 1998 IEEE, 3 pages			
Dk	13.	Hisamoto et al., "A Fully Depleted Lean-channel Transistor (DELTA)," 1989 IEEE, pp. 34.5.1 - 34.5.4			
Dk	14.	Li et al., "On the Growth of Highly Ordered Pores in Anodized Aluminum Oxide," Chem. Mater. 1998, Vol. 10, pp. 2470-2480			
Dk	15.	Masuda et al., "Highly ordered nanochannel-array architecture in anodic alumina," Appl. Phys. Lett. 71, No. 19, November 10, 1997, pp. 2770-2772			
Dk	16.	Risch et al., "Vertical MOS Transistors with 70nm Channel Length," IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498			
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Dk	19.	Backman et al., "Polarized Light Scattering Spectroscopy for Quantitative Measurement of Epithelial Cellular Structures <i>In Situ</i> ," IEEE Journal of Selected Topics in Quantum Electronics., Vol. 5, No. 4, July/August 1999, pp. 1019-1026			
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Dk	22.	Fafard et al., "Red-Emitting Semiconductor Quantum Dot Lasers," 2003 AAAS Annual Meeting Newsroom, February 13-18, 2002, 15 pages			

Examiner Signature		Date Considered	1-18-05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		Group Art Unit	2813
		Examiner Name	HOGANS
Sheet 2 of 2	Attorney Docket Number	5051-563DV	

DA	23.	Faist et al., "Mid-infrared field-tunable intersubband electroluminescence at room temperature by photon-assisted tunneling in coupled-quantum wells," Appl. Phys. Lett., Vol. 64, No. 9, February 28, 1994, pp. 1144-1146
DA	24.	Guha et al., "Selective area metalorganic molecular-beam epitaxy of GaN and the growth of luminescent microcolumns on Si/SiO <sub>2</sub> ," Applied Physics Letters, Vol. 75, No. 4, July 26, 1999, pp. 463-465
DA	25.	Hergenrother et al., "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length," 1999 IEEE, pp. IEDM 99-75 through 99-78
DA	26.	Hinzer et al., "Widely tunable self-assembled quantum dot lasers," J. Vac. Sci. Technol. A, Vol. 18, No. 2, Mar/Apr 2000, pp. 578-581
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DA	31.	Meindl, "Low Power Microelectronics: Retrospect and Prospect," Proceedings of the IEEE, Vol. 83, No. 4, April 1995, pp. 619-635
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DA	33.	Montgomery, "Annual Technology Forecast, Fifty years of fiber optics," Lightwave Special Reports, December 1999, pp. 49-54
DA	34.	Nam et al., "Lateral epitaxy of low defect density GaN layers via organometalliv vapor phase epitaxy," Applied Physics Letters, Vol. 71, No. 18, November 3, 1997, pp. 2638-2640
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DA	36.	Pan et al., "Normal-incidence intersubband (In, Ga)As/GaAs quantum dot infrared photodetectors," Applied Physics Letters, Vol. 73, No. 14, October 5, 1998, pp. 1937-1939
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DA	38.	Rogers et al., "Low threshold voltage continuous wave vertical-cavity surface-emitting lasers," Applied Physics Letters, Vol. 62, 1993, pp. 2027-2029
DA	39.	Sarlet et al., "Control of Widely Tunable SSG-DBR Lasers for Dense Wavelength Division Multiplexing," Journal of Lightwave Technology, Vol. 18, No. 8, August 2000, pp. 1128-1138
DA	40.	Ventkatesan et al., "A High Performance 1.8V, 0.20µm CMOS Technology with Copper Metallization," 1997 IEEE, pp. IEDM 97-769 through 97-772
DA	41.	Wong et al., "Device Design Considerations for Double-Gate, Ground-Plane, and Single-Gated Ultra-Thin SOI MOSFET's at the 25 nm Channel Length Generation," 1998 IEEE, pp. IEDM 98-407 through 98-410
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DA	45.	Nitayama et al., "Multi-Pillar SGT for Compact and High-Speed Circuits," IEEE Trans. E. Dev. 38 (3), 1991, pp. 579-583.

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